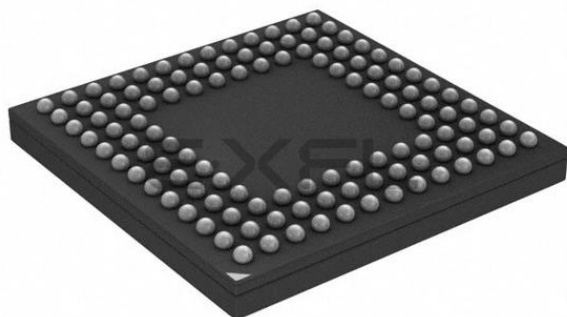




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I ² C, IrDA, LINbus, MMC/SD/SDIO, QSPI, SmartCard, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	95
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	512K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.8V
Data Converters	A/D 16x12b SAR; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	120-VFBGA
Supplier Device Package	120-BGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg11b840f1024gl120-a

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4. Electrical Specifications

4.1 Electrical Characteristics

All electrical parameters in all tables are specified under the following conditions, unless stated otherwise:

- Typical values are based on $T_{AMB}=25\text{ }^{\circ}\text{C}$ and $V_{DD}=3.3\text{ V}$, by production test and/or technology characterization.
- Minimum and maximum values represent the worst conditions across supply voltage, process variation, and operating temperature, unless stated otherwise.

Refer to [4.1.2.1 General Operating Conditions](#) for more details about operational supply and temperature limits.

4.1.10.2 High-Frequency Crystal Oscillator (HFXO)

Table 4.13. High-Frequency Crystal Oscillator (HFXO)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Crystal frequency	f_{HFXO}	No clock doubling	4	—	50	MHz
		Clock doubler enabled	TBD	—	TBD	MHz
Supported crystal equivalent series resistance (ESR)	ESR_{HFXO}	50 MHz crystal	—	—	50	Ω
		24 MHz crystal	—	—	150	Ω
		4 MHz crystal	—	—	180	Ω
Nominal on-chip tuning cap range ¹	$C_{\text{HFXO_T}}$	On each of HFXTAL_N and HFXTAL_P pins	8.7	—	51.7	pF
On-chip tuning capacitance step	SS_{HFXO}		—	0.084	—	pF
Startup time	t_{HFXO}	50 MHz crystal, ESR = 50 Ohm, $C_L = 8$ pF	—	350	—	μs
		24 MHz crystal, ESR = 150 Ohm, $C_L = 6$ pF	—	700	—	μs
		4 MHz crystal, ESR = 180 Ohm, $C_L = 18$ pF	—	3	—	ms
Current consumption after startup	I_{HFXO}	50 MHz crystal	—	880	—	μA
		24 MHz crystal	—	420	—	μA
		4 MHz crystal	—	80	—	μA

Note:

1. The effective load capacitance seen by the crystal will be $C_{\text{HFXO_T}}/2$. This is because each XTAL pin has a tuning cap and the two caps will be seen in series by the crystal.

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Frequency limits	f _{HFRCO_BAND}	FREQRANGE = 0, FINETUNING = 0	1	—	10	MHz
		FREQRANGE = 3, FINETUNING = 0	2	—	17	MHz
		FREQRANGE = 6, FINETUNING = 0	4	—	30	MHz
		FREQRANGE = 7, FINETUNING = 0	5	—	34	MHz
		FREQRANGE = 8, FINETUNING = 0	7	—	42	MHz
		FREQRANGE = 10, FINETUNING = 0	12	—	58	MHz
		FREQRANGE = 11, FINETUNING = 0	15	—	68	MHz
		FREQRANGE = 12, FINETUNING = 0	18	—	83	MHz
		FREQRANGE = 13, FINETUNING = 0	24	—	100	MHz
		FREQRANGE = 14, FINETUNING = 0	28	—	119	MHz
		FREQRANGE = 15, FINETUNING = 0	33	—	138	MHz
		FREQRANGE = 16, FINETUNING = 0	43	—	163	MHz

Note:
1. Maximum DPLL lock time ~ = 6 x (M+1) x t_{REF}, where t_{REF} is the reference clock period.

EBI Read Enable Output Timing

Timing applies to both EBI_REn and EBI_NANDREn for all addressing modes and both polarities. Output timing for EBI_AD applies only to multiplexed addressing modes D8A24ALE and D16A16ALE. All numbers are based on route locations 0,1,2 only (with all EBI alternate functions using the same location at the same time). Timing is specified at 10% and 90% of IOVDD, 25 pF external loading, and slew rate for all GPIO set to 6.

Table 4.38. EBI Read Enable Output Timing

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Output hold time, from trailing EBI_REn / EBI_NANDREn edge to EBI_AD, EBI_A, EBI_CS _n , EBI_BLn invalid	t _{OH_REn}	IOVDD ≥ 1.62 V	-23 + (RDHOLD * t _{HFCOR-ECLK})	—	—	ns
		IOVDD ≥ 3.0 V	-13 + (RDHOLD * t _{HFCOR-ECLK})	—	—	ns
Output setup time, from EBI_AD, EBI_A, EBI_CS _n , EBI_BLn valid to leading EBI_REn / EBI_NANDREn edge ¹	t _{OSU_REn}	IOVDD ≥ 1.62 V	-12 + (RDSETUP * t _{HFCOR-ECLK})	—	—	ns
		IOVDD ≥ 3.0 V	-11 + (RDSETUP * t _{HFCOR-ECLK})	—	—	ns
EBI_REn pulse width ^{1 2}	t _{WIDTH_REn}	IOVDD ≥ 1.62 V	-6 + (MAX(1, RDSTRB) * t _{HFCOR-ECLK})	—	—	ns
		IOVDD ≥ 3.0 V	-4 + (MAX(1, RDSTRB) * t _{HFCOR-ECLK})	—	—	ns

Note:

1. The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFRE=0. The leading edge of EBI_REn can be moved to the right by setting HALFRE=1. This decreases the length of t_{WIDTH_REn} and increases the length of t_{OSU_REn} by 1/2 * t_{HFCLKNODIV}.
2. When page mode is used, RDSTRB is replaced by RDPA for page hits.

QSPI DDR Mode Timing (Locations 1, 2)

Timing is specified with voltage scaling disabled, PHY-mode, route locations other than 0, TX DLL = 53, RX DLL = 88, 20-25 pF loading per GPIO, and slew rate for all GPIO set to 6, DRIVESTRENGTH = STRONG.

Table 4.57. QSPI DDR Mode Timing (Locations 1, 2)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Half SCLK period	T/2	HFXO	$(1/F_{SCLK}) * 0.4 - 0.4$	—	—	ns
		HFRCO, AUXHFRCO, USHFRCO	$(1/F_{SCLK}) * 0.44$	—	—	ns
Output valid	t_{OV}		—	—	T/2 - 6.6	ns
Output hold	t_{OH}		T/2 - 52.2	—	—	ns
Input setup	t_{SU}		44.8	—	—	ns
Input hold	t_H		-2.4	—	—	ns

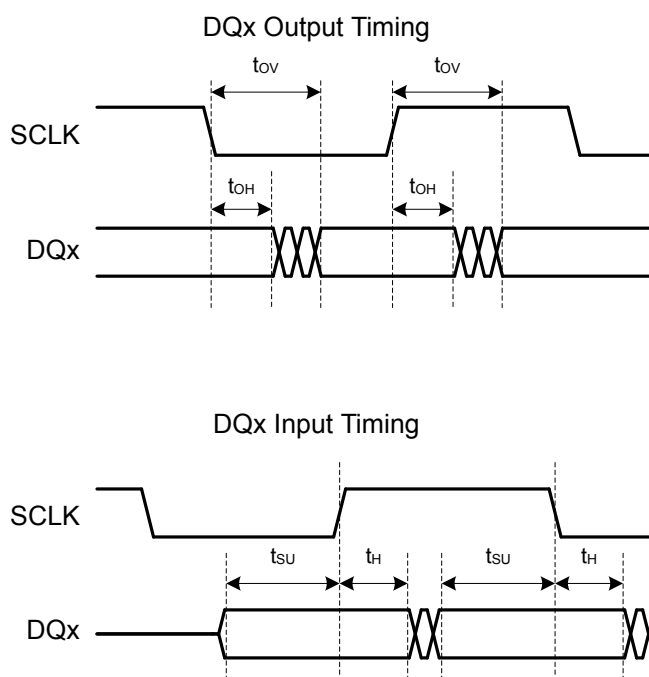


Figure 4.22. QSPI DDR Timing Diagrams

QSPI DDR Flash Timing Example

This example uses timing values for location 0 (DDR mode) to demonstrate the calculation of allowable flash timing using the QSPI in DDR mode.

- Using a configured SCLK frequency (F_{SCLK}) of 8 MHz from the HFXO clock source:
- The resulting minimum half-period, $T/2(\min) = (1/F_{SCLK}) * 0.4 - 0.4 = 49.6$ ns.
- Flash will see a minimum setup time of $T/2 - t_{OV} = T/2 - (T/2 - 5.0) = 5.0$ ns.
- Flash will see a minimum hold time of $t_{OH} = T/2 - 39.4 = 49.6 - 39.4 = 10.2$ ns.
- Flash can have a maximum output valid time of $T/2 - t_{SU} = T/2 - 33.1 = 49.6 - 33.1 = 16.5$ ns.
- Flash can have a minimum output hold time of $t_H = -0.9$ ns.

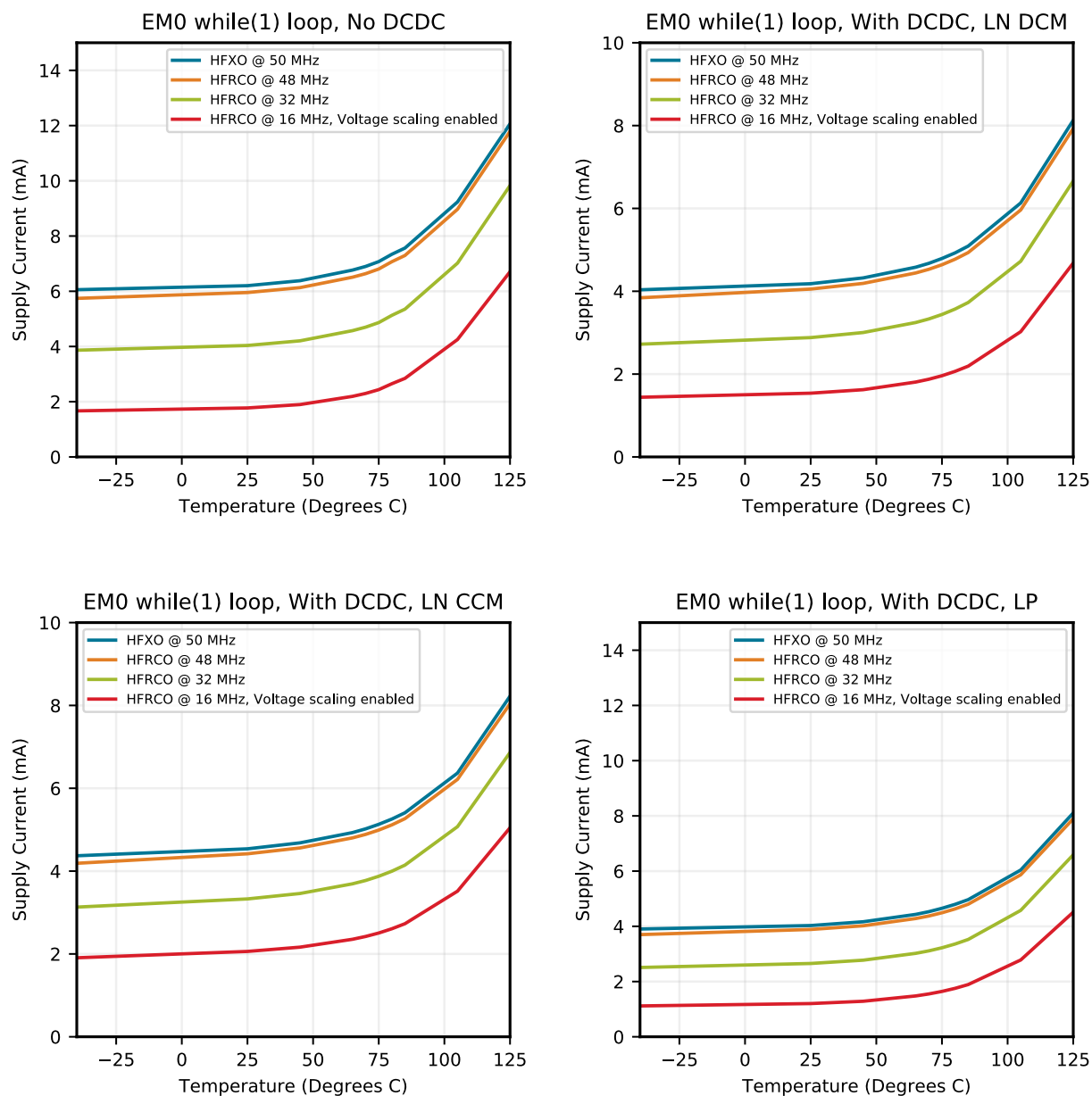


Figure 4.24. EM0 Active Mode Typical Supply Current vs. Temperature

5. Pin Definitions

5.1 EFM32GG11B8xx in BGA192 Device Pinout

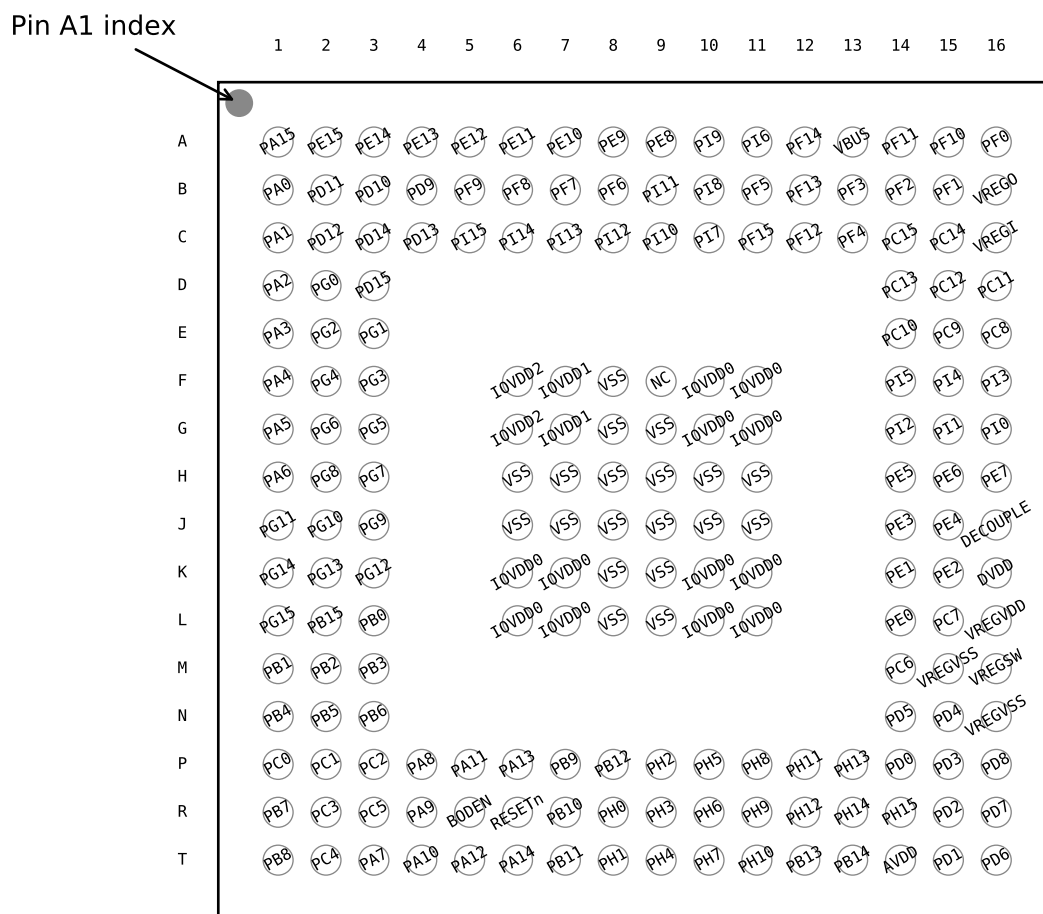


Figure 5.1. EFM32GG11B8xx in BGA192 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see [5.20 GPIO Functionality Table](#) or [5.21 Alternate Functionality Overview](#).

Table 5.1. EFM32GG11B8xx in BGA192 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PA15	A1	GPIO	PE15	A2	GPIO
PE14	A3	GPIO	PE13	A4	GPIO
PE12	A5	GPIO	PE11	A6	GPIO
PE10	A7	GPIO	PE9	A8	GPIO
PE8	A9	GPIO	PI9	A10	GPIO (5V)
PI6	A11	GPIO (5V)	PF14	A12	GPIO (5V)

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
VBUS	A13	USB VBUS signal and auxiliary input to 5 V regulator.	PF11	A14	GPIO (5V)
PF10	A15	GPIO (5V)	PF0	A16	GPIO (5V)
PA0	B1	GPIO	PD11	B2	GPIO
PD10	B3	GPIO	PD9	B4	GPIO
PF9	B5	GPIO	PF8	B6	GPIO
PF7	B7	GPIO	PF6	B8	GPIO
PI11	B9	GPIO (5V)	PI8	B10	GPIO (5V)
PF5	B11	GPIO	PF13	B12	GPIO (5V)
PF3	B13	GPIO	PF2	B14	GPIO
PF1	B15	GPIO (5V)	VREGO	B16	Decoupling for 5 V regulator and regulator output. Power for USB PHY in USB-enabled OPNs
PA1	C1	GPIO	PD12	C2	GPIO
PD14	C3	GPIO (5V)	PD13	C4	GPIO (5V)
PI15	C5	GPIO (5V)	PI14	C6	GPIO (5V)
PI13	C7	GPIO (5V)	PI12	C8	GPIO (5V)
PI10	C9	GPIO (5V)	PI7	C10	GPIO (5V)
PF15	C11	GPIO (5V)	PF12	C12	GPIO
PF4	C13	GPIO	PC15	C14	GPIO (5V)
PC14	C15	GPIO (5V)	VREGI	C16	Input to 5 V regulator.
PA2	D1	GPIO	PG0	D2	GPIO (5V)
PD15	D3	GPIO (5V)	PC13	D14	GPIO (5V)
PC12	D15	GPIO (5V)	PC11	D16	GPIO (5V)
PA3	E1	GPIO	PG2	E2	GPIO (5V)
PG1	E3	GPIO (5V)	PC10	E14	GPIO (5V)
PC9	E15	GPIO (5V)	PC8	E16	GPIO (5V)
PA4	F1	GPIO	PG4	F2	GPIO (5V)
PG3	F3	GPIO (5V)	IOVDD2	F6 G6	Digital IO power supply 2.

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PD8	H8	GPIO	PD5	H9	GPIO
PD6	H10	GPIO	PD7	H11	GPIO
PC1	J1	GPIO (5V)	PC3	J2	GPIO (5V)
PD15	J3	GPIO (5V)	PA12	J4	GPIO (5V)
PA9	J5	GPIO	PA10	J6	GPIO
PB9	J7	GPIO (5V)	PB10	J8	GPIO (5V)
PD2	J9	GPIO (5V)	PD3	J10	GPIO
PD4	J11	GPIO	PB7	K1	GPIO
PC4	K2	GPIO	PA13	K3	GPIO (5V)
PA11	K5	GPIO	RESETn	K6	Reset input, active low. To apply an external reset source to this pin, it is required to only drive this pin low during reset, and let the internal pull-up ensure that reset is released.
AVDD	K8 K9 L10	Analog power supply.	PD1	K11	GPIO
PB8	L1	GPIO	PC5	L2	GPIO
PA14	L3	GPIO	PB11	L5	GPIO
PB12	L6	GPIO	PB13	L8	GPIO
PB14	L9	GPIO	PD0	L11	GPIO (5V)

Note:

1. GPIO with 5V tolerance are indicated by (5V).
2. The pins PD13, PD14, and PD15 will not be 5V tolerant on all future devices. In order to preserve upgrade options with full hardware compatibility, do not use these pins with 5V domains.

5.9 EFM32GG11B5xx in QFP100 Device Pinout

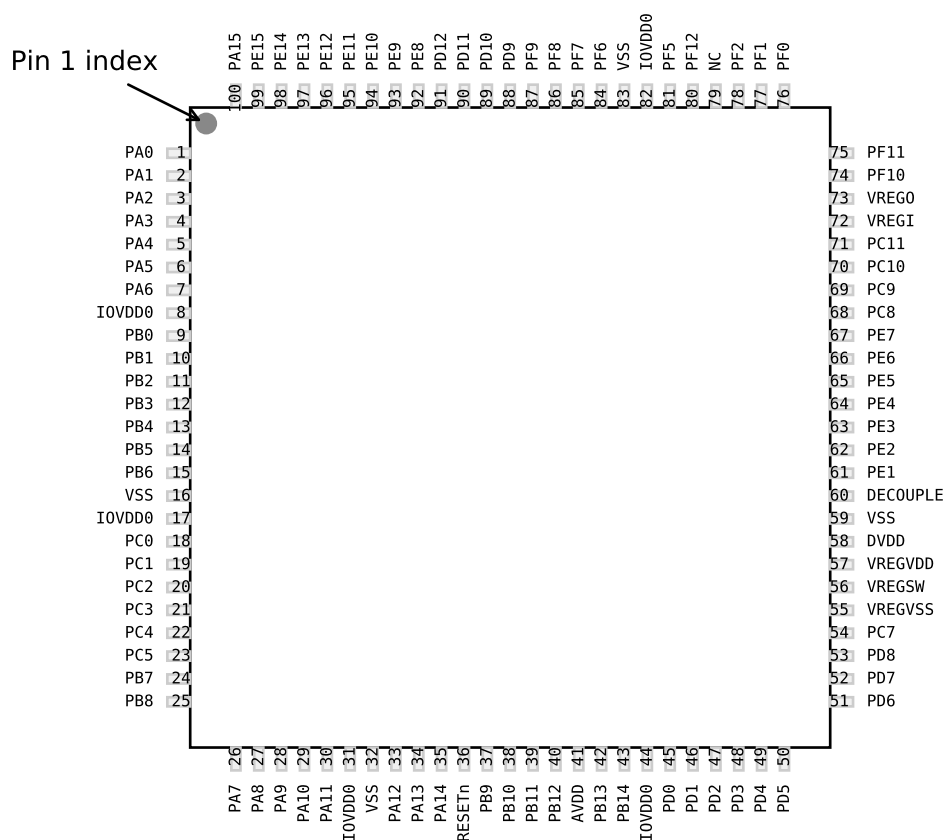


Figure 5.9. EFM32GG11B5xx in QFP100 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see [5.20 GPIO Functionality Table](#) or [5.21 Alternate Functionality Overview](#).

Table 5.9. EFM32GG11B5xx in QFP100 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PA0	1	GPIO	PA1	2	GPIO
PA2	3	GPIO	PA3	4	GPIO
PA4	5	GPIO	PA5	6	GPIO
PA6	7	GPIO	IOVDD0	8 17 31 44 82	Digital IO power supply 0.
PB0	9	GPIO	PB1	10	GPIO

Alternate	LOCATION		
Functionality	0 - 3	4 - 7	Description
ETH_MDIO	0: PB3 1: PD13 2: PC0 3: PA15		Ethernet Management Data I/O.
ETH_MIICOL	0: PB2 1: PG15 2: PB4		Ethernet MII Collision Detect.
ETH_MIICRS	0: PB1 1: PG14 2: PB3		Ethernet MII Carrier Sense.
ETH_MIIRXCLK	0: PA15 1: PG7 2: PD12		Ethernet MII Receive Clock.
ETH_MIIRXD0	0: PE12 1: PG11 2: PF9		Ethernet MII Receive Data Bit 0.
ETH_MIIRXD1	0: PE13 1: PG10 2: PD9		Ethernet MII Receive Data Bit 1.
ETH_MIIRXD2	0: PE14 1: PG9 2: PD10		Ethernet MII Receive Data Bit 2.
ETH_MIIRXD3	0: PE15 1: PG8 2: PD11		Ethernet MII Receive Data Bit 3.
ETH_MIIRXDV	0: PE11 1: PG12 2: PF8		Ethernet MII Receive Data Valid.
ETH_MIIRXER	0: PE10 1: PG13 2: PF7		Ethernet MII Receive Error.
ETH_MIITXCLK	0: PA0 1: PG0		Ethernet MII Transmit Clock.
ETH_MIITXD0	0: PA4 1: PG4		Ethernet MII Transmit Data Bit 0.
ETH_MIITXD1	0: PA3 1: PG3		Ethernet MII Transmit Data Bit 1.

Alternate	LOCATION		
Functionality	0 - 3	4 - 7	Description
LFXTAL_N	0: PB8		Low Frequency Crystal (typically 32.768 kHz) negative pin. Also used as an optional external clock input pin.
LFXTAL_P	0: PB7		Low Frequency Crystal (typically 32.768 kHz) positive pin.
OPA0_N	0: PC5		Operational Amplifier 0 external negative input.
OPA0_P	0: PC4		Operational Amplifier 0 external positive input.
OPA1_N	0: PD7		Operational Amplifier 1 external negative input.
OPA1_P	0: PD6		Operational Amplifier 1 external positive input.
OPA2_N	0: PD3		Operational Amplifier 2 external negative input.
OPA2_OUT	0: PD5		Operational Amplifier 2 output.
OPA2_OUTALT	0: PD0		Operational Amplifier 2 alternative output.
OPA2_P	0: PD4		Operational Amplifier 2 external positive input.
OPA3_N	0: PC7		Operational Amplifier 3 external negative input.
OPA3_OUT	0: PD1		Operational Amplifier 3 output.
OPA3_P	0: PC6		Operational Amplifier 3 external positive input.

Alternate	LOCATION		
Functionality	0 - 3	4 - 7	Description
WTIM0_CC2	0: PE6 1: PD14 2: PG4 3: PG10	4: PF1 5: PB2 6: PB5 7: PC3	Wide timer 0 Capture Compare input / output channel 2.
WTIM0_CDTI0	0: PE10 1: PD15 2: PA12 3: PG11	4: PD4	Wide timer 0 Complimentary Dead Time Insertion channel 0.
WTIM0_CDTI1	0: PE11 1: PG0 2: PA13 3: PG12	4: PD5	Wide timer 0 Complimentary Dead Time Insertion channel 1.
WTIM0_CDTI2	0: PE12 1: PG1 2: PA14 3: PG13	4: PD6	Wide timer 0 Complimentary Dead Time Insertion channel 2.
WTIM1_CC0	0: PB13 1: PD2 2: PD6 3: PC7	4: PE3 5: PE7 6: PH8 7: PH12	Wide timer 1 Capture Compare input / output channel 0.
WTIM1_CC1	0: PB14 1: PD3 2: PD7 3: PE0	4: PE4 5: PI0 6: PH9 7: PH13	Wide timer 1 Capture Compare input / output channel 1.
WTIM1_CC2	0: PD0 1: PD4 2: PD8 3: PE1	4: PE5 5: PI1 6: PH10 7: PH14	Wide timer 1 Capture Compare input / output channel 2.
WTIM1_CC3	0: PD1 1: PD5 2: PC6 3: PE2	4: PE6 5: PI2 6: PH11 7: PH15	Wide timer 1 Capture Compare input / output channel 3.
WTIM2_CC0	0: PA9 1: PA12 2: PB9 3: PB12	4: PG14 5: PD3 6: PH4 7: PH7	Wide timer 2 Capture Compare input / output channel 0.
WTIM2_CC1	0: PA10 1: PA13 2: PB10 3: PG12	4: PG15 5: PD4 6: PH5 7: PH8	Wide timer 2 Capture Compare input / output channel 1.
WTIM2_CC2	0: PA11 1: PA14 2: PB11 3: PG13	4: PH0 5: PD5 6: PH6 7: PH9	Wide timer 2 Capture Compare input / output channel 2.
WTIM3_CC0	0: PD9 1: PC8 2: PC11 3: PC14	4: PI3 5: PI6 6: PB6 7: PF13	Wide timer 3 Capture Compare input / output channel 0.
WTIM3_CC1	0: PD10 1: PC9 2: PC12 3: PF10	4: PI4 5: PI7 6: PF4 7: PF14	Wide timer 3 Capture Compare input / output channel 1.

7. BGA152 Package Specifications

7.1 BGA152 Package Dimensions

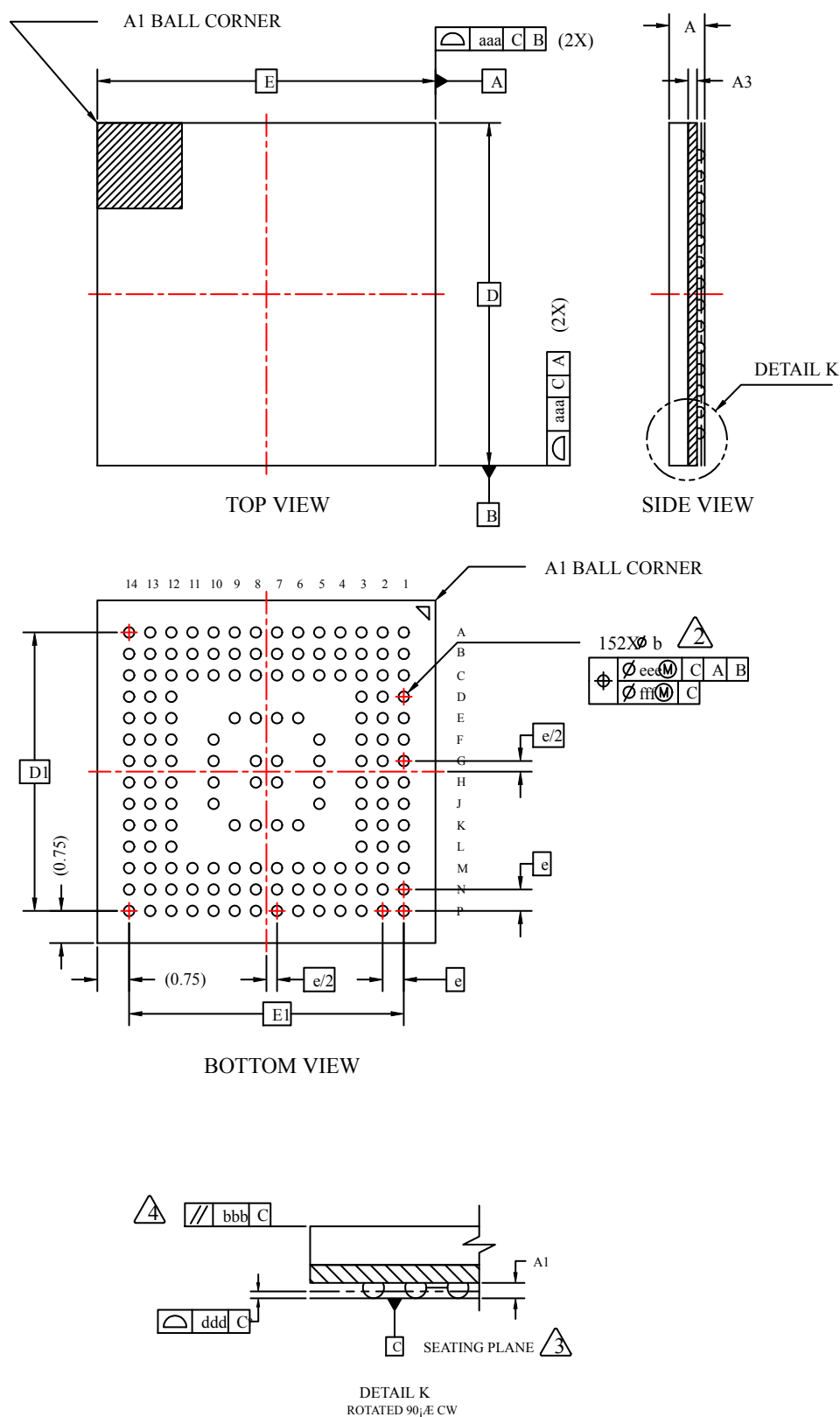


Figure 7.1. BGA152 Package Drawing

Table 7.1. BGA152 Package Dimensions

Dimension	Min	Typ	Max
A	0.78	0.84	0.90
A1	0.13	0.18	0.23
A3	0.16	0.20	0.24
A2	0.45 REF		
D	8.00 BSC		
e	0.50 BSC		
E	8.00 BSC		
D1	6.50 BSC		
E1	6.50 BSC		
b	0.20	0.25	0.30
aaa	0.10		
bbb	0.10		
ddd	0.08		
eee	0.15		
fff	0.05		

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

Table 9.1. BGA112 Package Dimensions

Dimension	Min	Typ	Max
A	-	-	1.30
A1	0.55	0.60	0.65
A2	0.21 BSC		
A3	0.30	0.35	0.40
d	0.43	0.48	0.53
D	10.00 BSC		
D1	8.00 BSC		
E	10.00 BSC		
E1	8.00 BSC		
e1	0.80 BSC		
e2	0.80 BSC		
L1	1.00 REF		
L2	1.00 REF		

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

Table 10.2. TQFP100 PCB Land Pattern Dimensions

Dimension	Min	Nom	Max
C1		15.4	
C2		15.4	
E		0.50 BSC	
X		0.30	
Y		1.50	

Note:

- 1. All dimensions shown are in millimeters (mm) unless otherwise noted.
- 2. This Land Pattern Design is based on the IPC-7351 guidelines.
- 3. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.
- 4. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
- 5. The stencil thickness should be 0.125 mm (5 mils).
- 6. The ratio of stencil aperture to land pad size should be 1:1 for all perimeter pads.
- 7. A No-Clean, Type-3 solder paste is recommended.
- 8. The recommended card reflow profile is per the JEDEC/IPC J-STD-020C specification for Small Body Components.

10.3 TQFP100 Package Marking



Figure 10.3. TQFP100 Package Marking

The package marking consists of:

- P P P P P P P P P P – The part number designation.
- T T T T T T – A trace or manufacturing code. The first letter is the device revision.
- Y Y – The last 2 digits of the assembly year.
- W W – The 2-digit workweek when the device was assembled.

Table 12.2. QFN64 PCB Land Pattern Dimensions

Dimension	Typ
C1	8.90
C2	8.90
E	0.50
X1	0.30
Y1	0.85
X2	7.30
Y2	7.30

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. This Land Pattern Design is based on the IPC-7351 guidelines.
3. All dimensions shown are at Maximum Material Condition (MMC). Least Material Condition (LMC) is calculated based on a Fabrication Allowance of 0.05mm.
4. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 μ m minimum, all the way around the pad.
5. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
6. The stencil thickness should be 0.125 mm (5 mils).
7. The ratio of stencil aperture to land pad size can be 1:1 for all pads.
8. A 3x3 array of 1.45 mm square openings on a 2.00 mm pitch can be used for the center ground pad.
9. A No-Clean, Type-3 solder paste is recommended.
10. The recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

13. Revision History

Revision 0.6

March, 2018

- Removed "Confidential" watermark.
- Updated [4.1 Electrical Characteristics](#) and [4.2 Typical Performance Curves](#) with latest characterization data.

Revision 0.2

October, 2017

- Updated memory maps to latest formatting and to include all peripherals.
- Updated all electrical specifications tables with latest characterization results.
- **Absolute Maximum Ratings** Table:
 - Removed redundant I_{VSSMAX} line.
 - Added footnote to clarify V_{DIGPIN} specification for 5V tolerant GPIO.
- **General Operating Conditions** Table:
 - Removed dV_{DD} specification and redundant footnote about shorting VREGVDD and AVDD together.
 - Added footnote about IOVDD voltage restriction when CSEN peripheral is used with chopping enabled.
- **Flash Memory Characteristics** Table: Added timing measurement clarification for Device Erase and Mass Erase.
- **Analog to Digital Converter (ADC)** Table:
 - Added header text for general specification conditions.
 - Added footnote for clarification of input voltage limits.
- Minor typographical corrections, including capitalization, mis-spellings and punctuation marks, throughout document.
- Minor formatting and styling updates, including table formats, TOC location, and boilerplate information throughout document.

Revision 0.1

April 27th, 2017

Initial release.